

CSD17559Q5 30-V N-Channel NexFET™ Power MOSFET

1 Features

- Extremely Low Resistance
- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5 mm × 6 mm Plastic Package

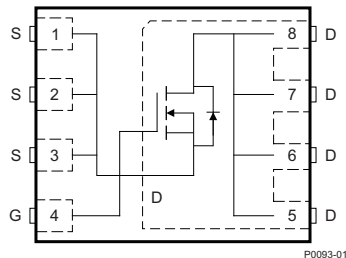
2 Applications

- Point of Load Synchronous Buck in Networking, Telecom, and Computing Systems
- Synchronous Rectification
- Active ORing and Hotswap Applications

3 Description

This 30 V, 0.95 mΩ, 5 × 6 mm SON NexFET™ power MOSFET is designed to minimize losses in synchronous rectification and other power conversion applications.

Top View



P0093-01

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	30		V
Q_g	Gate Charge Total (4.5 V)	39		nC
Q_{gd}	Gate Charge Gate-to-Drain	9.3		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 4.5\text{ V}$	1.15	mΩ
		$V_{GS} = 10\text{ V}$	0.95	mΩ
$V_{GS(th)}$	Threshold Voltage	1.4		V

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship
CSD17559Q5	2500	13-Inch Reel	SON 5 × 6 mm Plastic Package	Tape and Reel
CSD17559Q5T	250	13-Inch Reel		

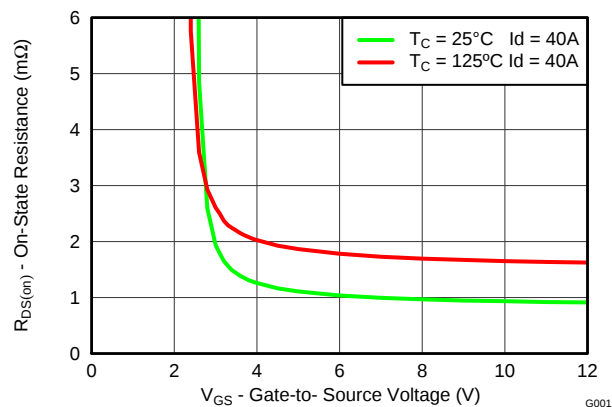
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited)	100	A
	Continuous Drain Current (Silicon limited), $T_C = 25^\circ\text{C}$	257	
	Continuous Drain Current ⁽¹⁾	40	
I_{DM}	Pulsed Drain Current ⁽²⁾	400	A
P_D	Power Dissipation ⁽¹⁾	3.2	W
	Power Dissipation, $T_C = 25^\circ\text{C}$	96	
T_J , T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse $I_D = 104\text{ A}$, $L = 0.1\text{ mH}$, $R_G = 25\ \Omega$	541	mJ

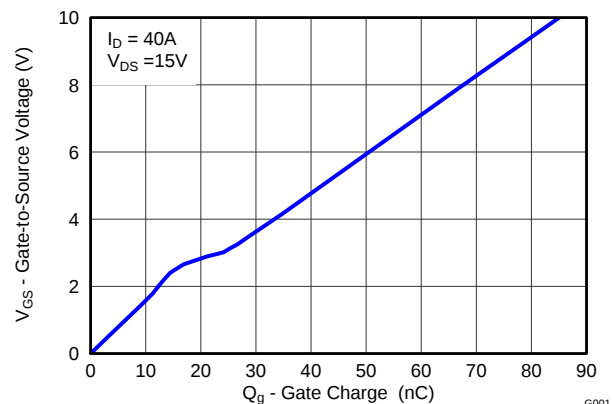
(1) Typical $R_{\theta JA} = 40^\circ\text{C/W}$ on 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 0.06 inch (1.52 mm) thick FR4 PCB.

(2) Max $R_{\theta JC} = 1.2^\circ\text{C/W}$, pulse duration ≤100 μs, duty cycle ≤1%

 $R_{DS(on)}$ vs V_{GS} 

G001

Gate Charge



G001



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4 Revision History

Changes from Original (November 2012) to Revision A	Page
•	1
• Added small reel information	1
• Increased max pulsed drain current to 400 A	1
• Added line for max power dissipation with case temperature held to 25°.....	1
• Updated max pulsed current conditions	1
• Updated Figure 1 to a normalized $R_{\theta JC}$ curve	4
• Updated the SOA in Figure 10	6

5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

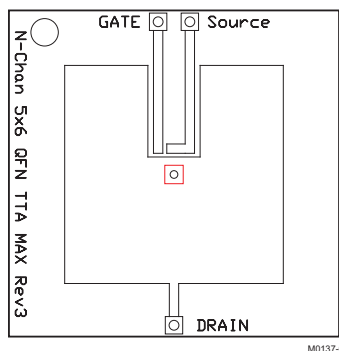
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	30			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 24 V			1	μA
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	1.2	1.4	1.7	V
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 4.5 V, I _{DS} = 40 A	1.15		1.5	mΩ
		V _{GS} = 10 V, I _{DS} = 40 A	0.95		1.15	mΩ
g _{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 40 A	235			S
DYNAMIC CHARACTERISTICS						
C _{iSS}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz	7070		9200	pF
C _{oSS}	Output Capacitance		1780		2314	pF
C _{rSS}	Reverse Transfer Capacitance		87		113	pF
R _G	Series Gate Resistance		1.2		2.4	Ω
Q _g	Gate Charge Total (4.5 V)	V _{DS} = 15 V, I _{DS} = 40 A	39		51	nC
Q _{gd}	Gate Charge Gate-to-Drain		9.3			nC
Q _{gs}	Gate Charge Gate-to-Source		14.4			nC
Q _{g(th)}	Gate Charge at V _{th}		8.3			nC
Q _{oSS}	Output Charge	V _{DS} = 15 V, V _{GS} = 0 V	50			nC
t _{d(on)}	Turn On Delay Time	V _{DS} = 15 V, V _{GS} = 4.5 V, I _{DS} = 40 A, R _G = 2 Ω	20			ns
t _r	Rise Time		41			ns
t _{d(off)}	Turn Off Delay Time		32			ns
t _f	Fall Time		14			ns
DIODE CHARACTERISTICS						
V _{SD}	Diode Forward Voltage	I _{SD} = 40 A, V _{GS} = 0 V	0.8		1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 15 V, I _F = 40 A, di/dt = 300 A/μs	80			nC
t _{rr}	Reverse Recovery Time		37			ns

5.2 Thermal Information

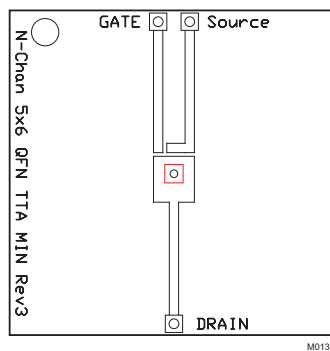
(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
R _{θJC}	Junction-to-Case Thermal Resistance ⁽¹⁾			1.2	°C/W
R _{θJA}	Junction-to-Ambient Thermal Resistance ⁽¹⁾⁽²⁾			50	

- (1) R_{θJC} is determined with the device mounted on a 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inches × 1.5 inches (3.81 cm × 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu.



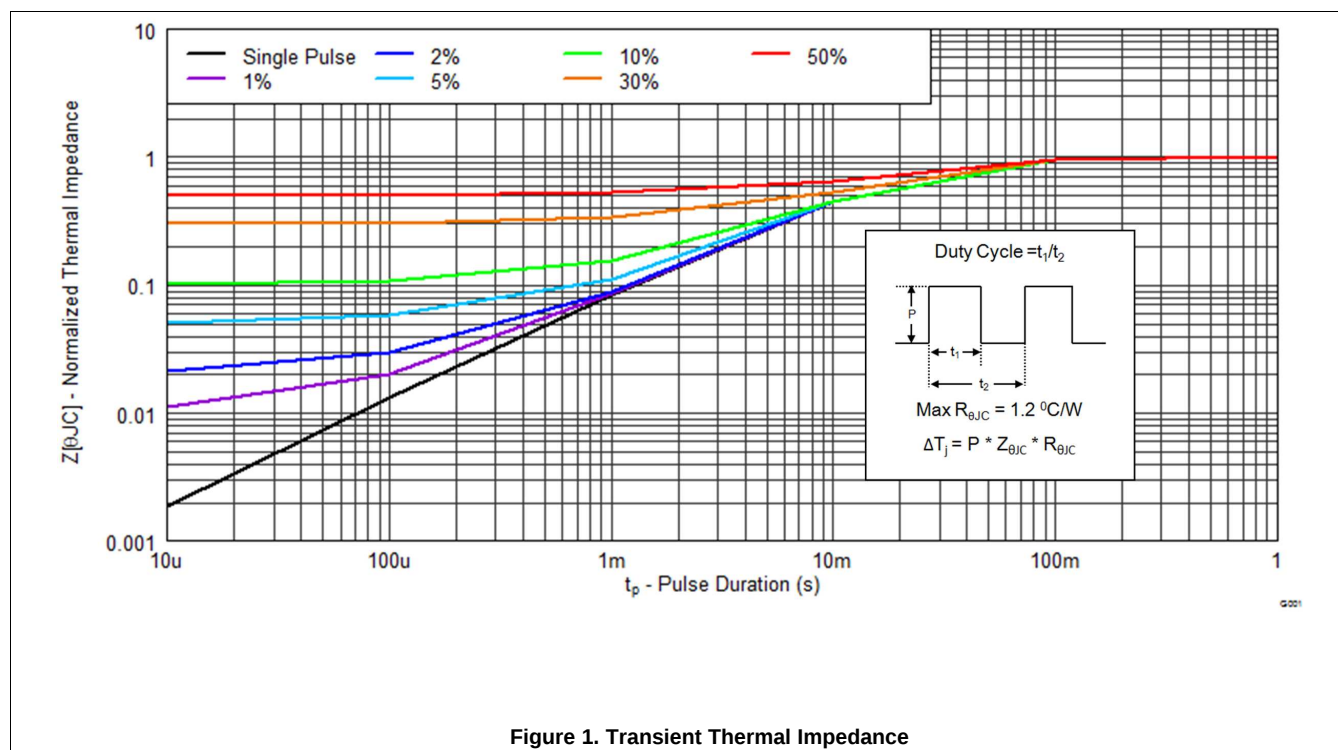
Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on
1 inch² (6.45 cm²) of
2-oz. (0.071-mm thick)
Cu.



Max $R_{\theta JA} = 125^{\circ}\text{C/W}$
when mounted on a
minimum pad area of
2-oz. (0.071-mm thick)
Cu.

5.3 Typical MOSFET Characteristics

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

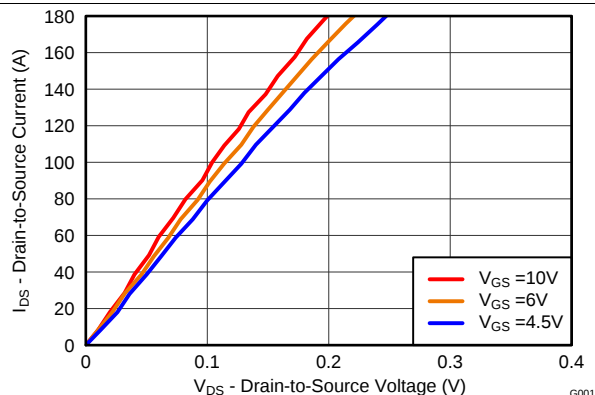


Figure 2. Saturation Characteristics

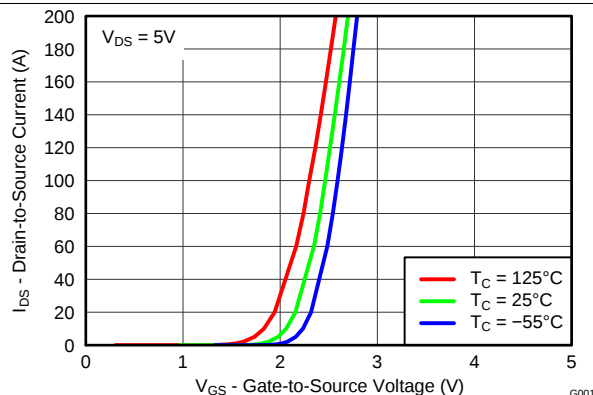


Figure 3. Transfer Characteristics

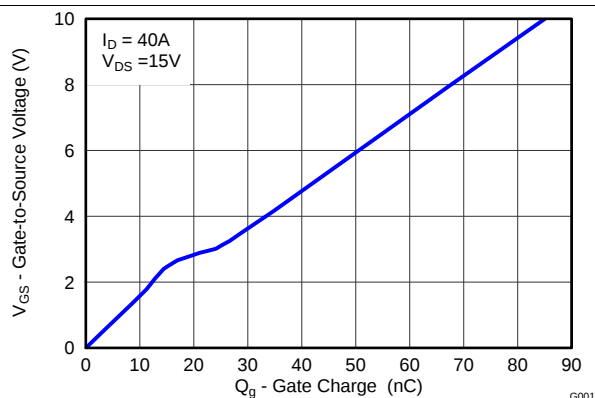


Figure 4. Gate Charge

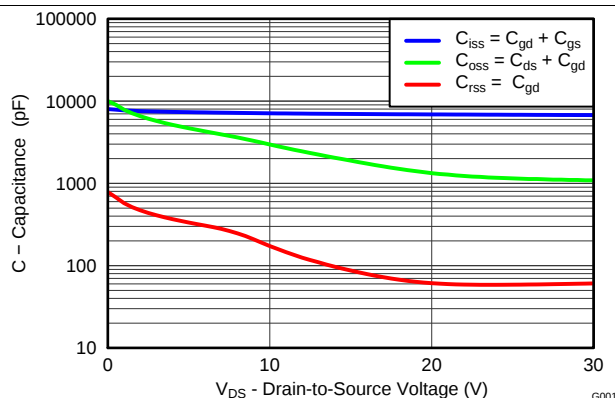


Figure 5. Capacitance

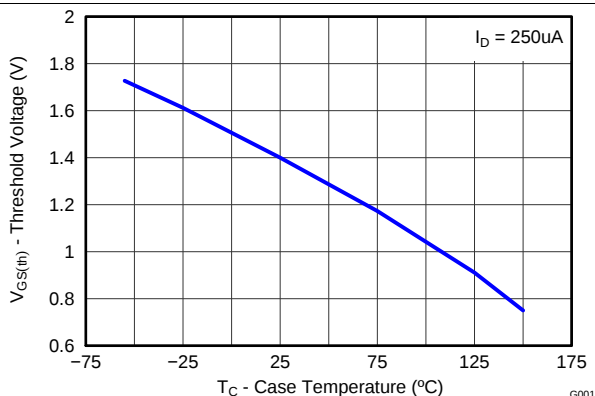


Figure 6. Threshold Voltage vs Temperature

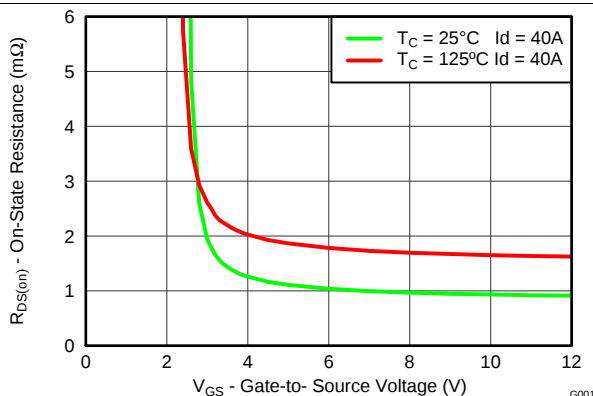


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

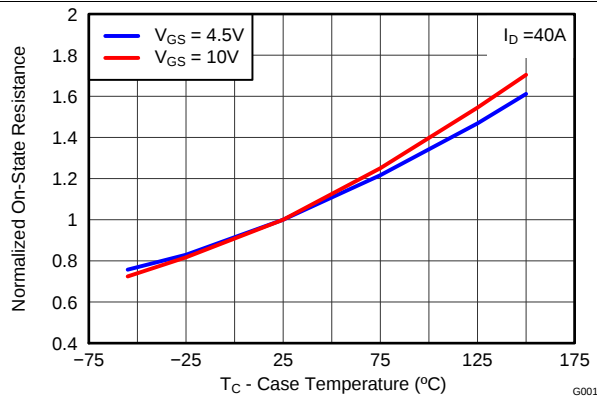


Figure 8. Normalized On-State Resistance vs Temperature

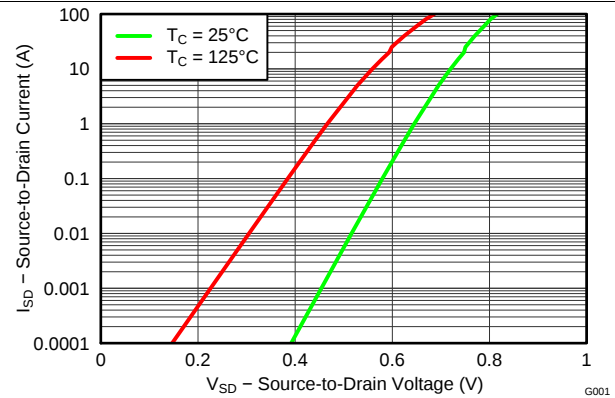


Figure 9. Typical Diode Forward Voltage

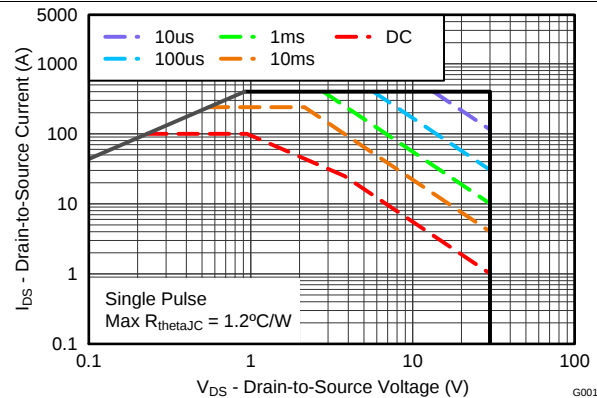


Figure 10. Safety Operating Area

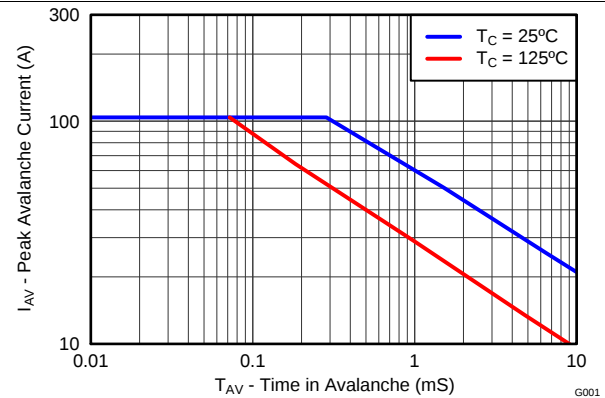


Figure 11. Single Pulse Unclamped Inductive Switching

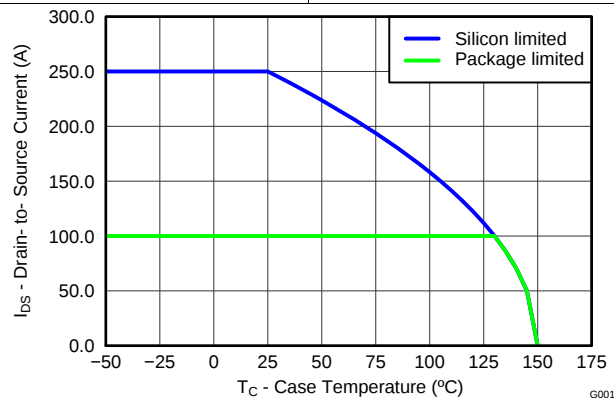


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

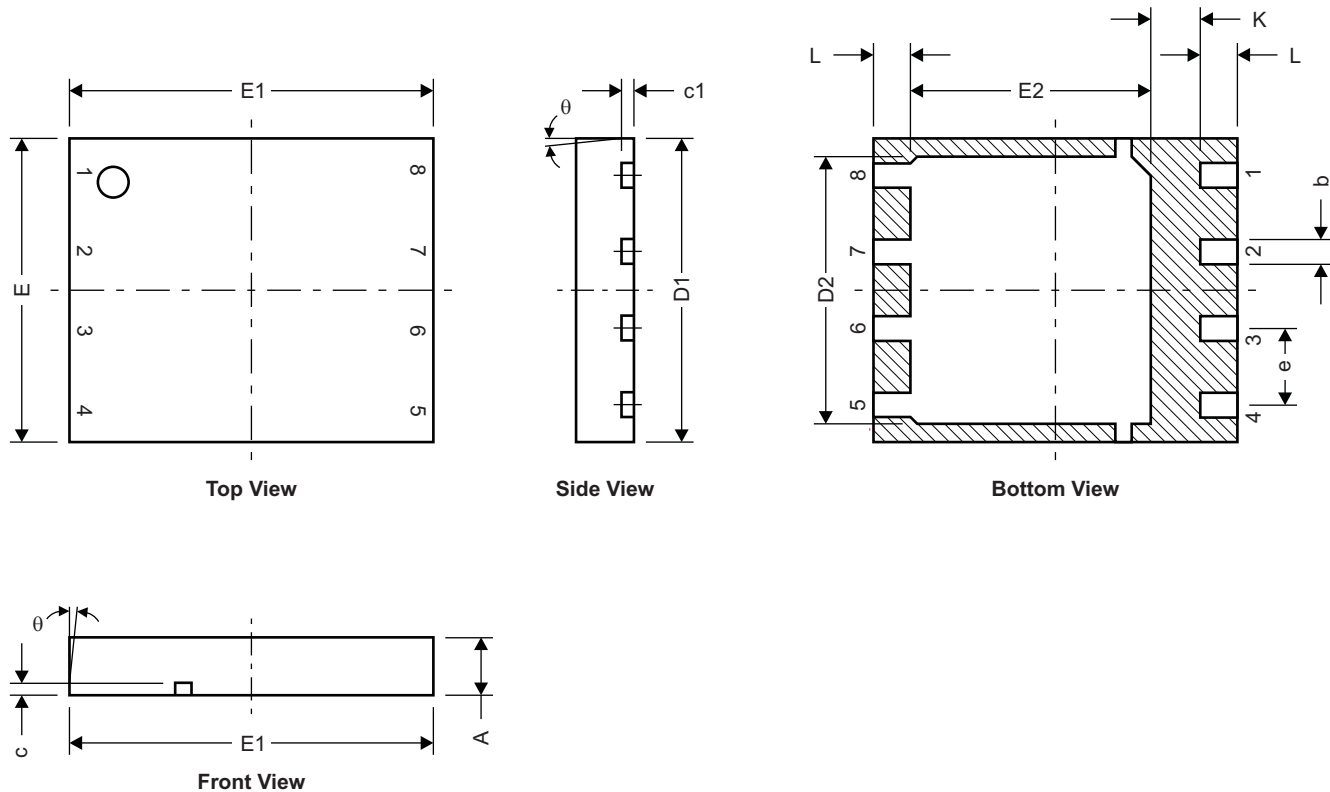
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

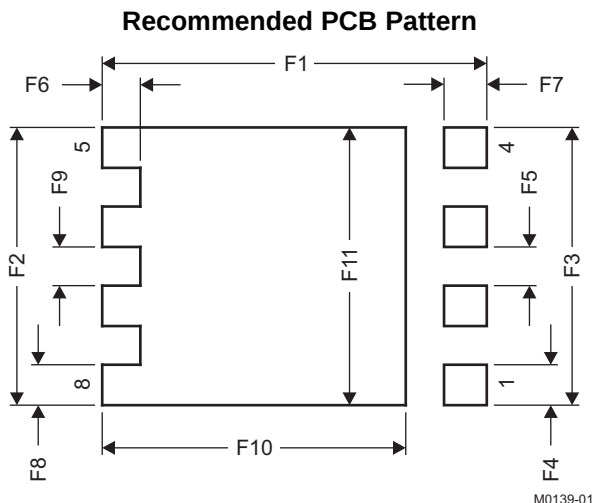
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5 Package Dimensions



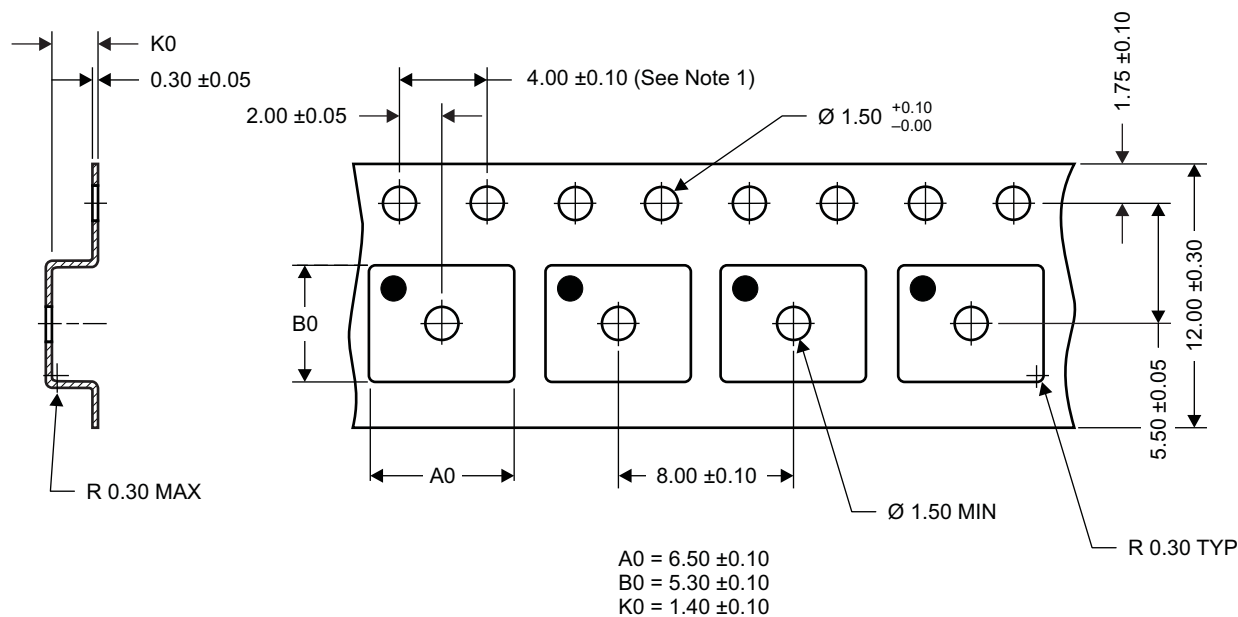
M0140-01

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00	—	—	—



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

7.2 Q5 Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ± 0.2
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm, unless otherwise specified.
5. Thickness: 0.30 ± 0.05 mm
6. MSL1 260°C (IR and convection) PbF-reflow compatible.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD17559Q5	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17559
CSD17559Q5.B	Active	Production	VSON-CLIP (DQH) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17559
CSD17559Q5T	Active	Production	VSON-CLIP (DQH) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17559
CSD17559Q5T.B	Active	Production	VSON-CLIP (DQH) 8	250 SMALL T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17559

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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